

July 2012

FDMQ8403

GreenBridgeTM Series of High-Efficiency Bridge Rectifiers N-Channel PowerTrench[®] MOSFET 100 V, 6 A, 110 m Ω

Features

- Max $r_{DS(on)}$ = 110 m Ω at V_{GS} = 10 V, I_D = 3 A
- Max $r_{DS(on)}$ = 175 m Ω at V_{GS} = 6 V, I_D = 2.4 A
- Substantial efficiency benefit in PD solutions
- RoHS Compliant

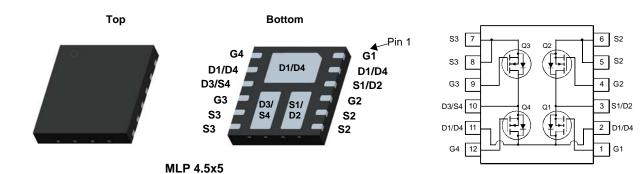
General Description

This quad MOSFET solution provides ten-fold improvement in power dissipation over diode bridge.

Application

■ High-Efficiency Bridge Rectifiers





MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter			Ratings	Units
V _{DS}	Drain to Source Voltage			100	V
V_{GS}	Gate to Source Voltage			±20	V
	Drain Current -Continuous (Package limited)	T _C = 25 °C		6	
I _D	-Continuous (Silicon limited)	T _C = 25 °C		9	Δ.
	-Continuous	T _A = 25 °C	(Note 1a)	3.1	A
	-Pulsed			12	
Б	Power Dissipation	T _C = 25 °C		17	W
P_{D}	Power Dissipation	T _A = 25 °C	(Note 1a)	1.9	VV
T _J , T _{STG}	Operating and Storage Junction Temperature Ra	inge		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	65	°C/M
R_{\thetaJA}	Thermal Resistance, Junction to Ambient	(Note 1b)	135	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMQ8403	FDMQ8403	MLP 4.5x5	13 "	12 mm	3000 units

Electrical Characteristics $T_J = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, referenced to 25 °C		72		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 80 V, V _{GS} = 0 V			1	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

On Characteristics

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	2	2.8	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μ A, referenced to 25 °C		-8		mV/°C
		$V_{GS} = 10 \text{ V}, I_D = 3 \text{ A}$		85	110	
r _{DS(on)}	r _{DS(on)} Static Drain to Source On Resistance	$V_{GS} = 6 \text{ V}, I_D = 2.4 \text{ A}$		115	175	mΩ
		$V_{GS} = 10 \text{ V}, I_D = 3 \text{ A}, T_J = 125 ^{\circ}\text{C}$		147	191	
9 _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 3 A		6		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 50 V V 0 V	162	215	pF
C _{oss}	Output Capacitance	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz	43	60	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 101112	2.6	5	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		4.1	10	ns
t _r	Rise Time	$V_{DD} = 50 \text{ V}, I_D = 3 \text{ A},$	1.2	10	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$	7.2	15	ns
t _f	Fall Time		1.8	10	ns
Q_g	Total Gate Charge	V _{GS} = 0 V to 10 V	3	5	nC
Qg	Total Gate Charge	$V_{GS} = 0 \text{ V to 5 V}$ $V_{DD} = 50 \text{ V},$	1.7	3	nC
Q _{gs}	Gate to Source Charge	I _D = 3 A	0.9		nC
Q_{gd}	Gate to Drain "Miller" Charge		0.8		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 3 \text{ A}$ (Note 2)		0.86	1.3	V
t _{rr}	Reverse Recovery Time	I _F = 3 A, di/dt = 100 A/μs		33	53	ns
Q _{rr}	Reverse Recovery Charge			23	37	nC

Notes:

¹ R_{0,JA} is determined with the device mounted on a 1in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{0,JC} is guaranteed by design while R_{0CA} is determined by the user's board design.



a. 65 °C/W when mounted on a 1 in² pad of 2 oz copper. the board designed Q1+Q3 or Q2+Q4.



 b. 135 °C/W when mounted on a minimum pad of 2 oz copper. the board designed Q1+Q3 or Q2+Q4.

^{2.} Pulse Test: Pulse Width < 300 $\mu\text{s},$ Duty cycle < 2.0%.

Typical Characteristics $T_J = 25$ °C unless otherwise noted

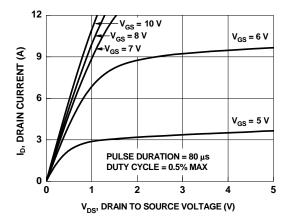


Figure 1. On Region Characteristics

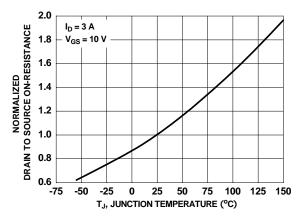


Figure 3. Normalized On Resistance vs Junction Temperature

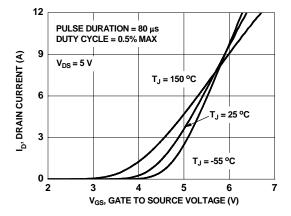


Figure 5. Transfer Characteristics

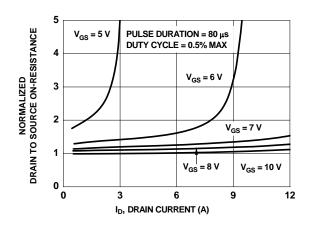


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

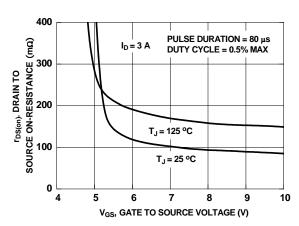


Figure 4. On-Resistance vs Gate to Source Voltage

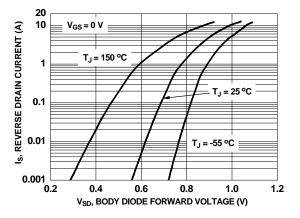


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25$ °C unless otherwise noted

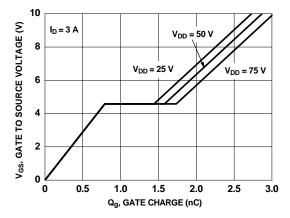


Figure 7. Gate Charge Characteristics

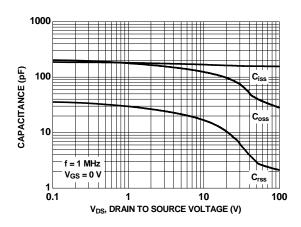


Figure 8. Capacitance vs Drain to Source Voltage

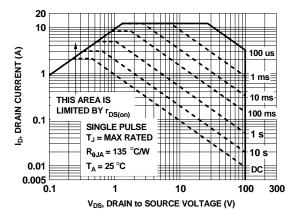


Figure 9. Forward Bias Safe Operating Area

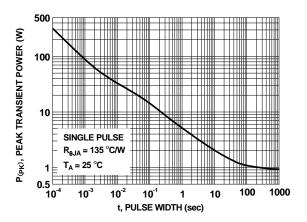


Figure 10. Single Pulse Maximum Power Dissipation

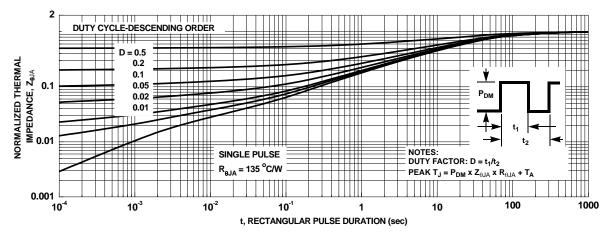
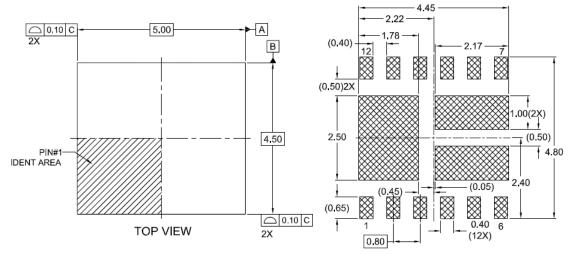
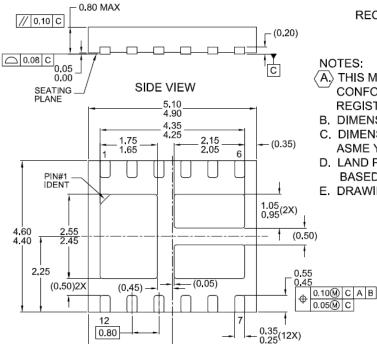


Figure 11. Junction-to-Ambient Transient Thermal Response Curve

Dimensional Outline and Pad Layout





2.50

BOTTOM VIEW

RECOMMENDED LAND PATTERN

NOTES:

- $\langle \overline{\mathsf{A}}
 angle$ THIS MKT. DWG. DOES NOT FULLY CONFORM TO JEDEC MO-229 REGISTRATION
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- D. LAND PATTERN RECOMMENDATION IS BASED ON FSC DESIGN ONLY.
- E. DRAWING FILENAME: MKT-MLP12FRev1.





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